

CHEMICAL-MECHANICAL PLANARIZATION OF BARRIERS OR LINERS FOR COPPER METALLURGY

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Abstract of the Disclosure

A tantalum-based liner for copper metallurgy is selectively removed by chemical-mechanical planarization (CMP) in an acidic slurry of an oxidizer such as hydrogen peroxide, deionized water, a corrosion inhibitor such as BTA, and a surfactant such as Duponol SP, resulting in a high removal rate of the liner without appreciable removal of the exposed copper and with minimal dishing.

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